

Supplementary Information for

The electronic transport properties of zigzag phosphorene-like MX (M=Ge/Sn, X=S/Se) nanostructures

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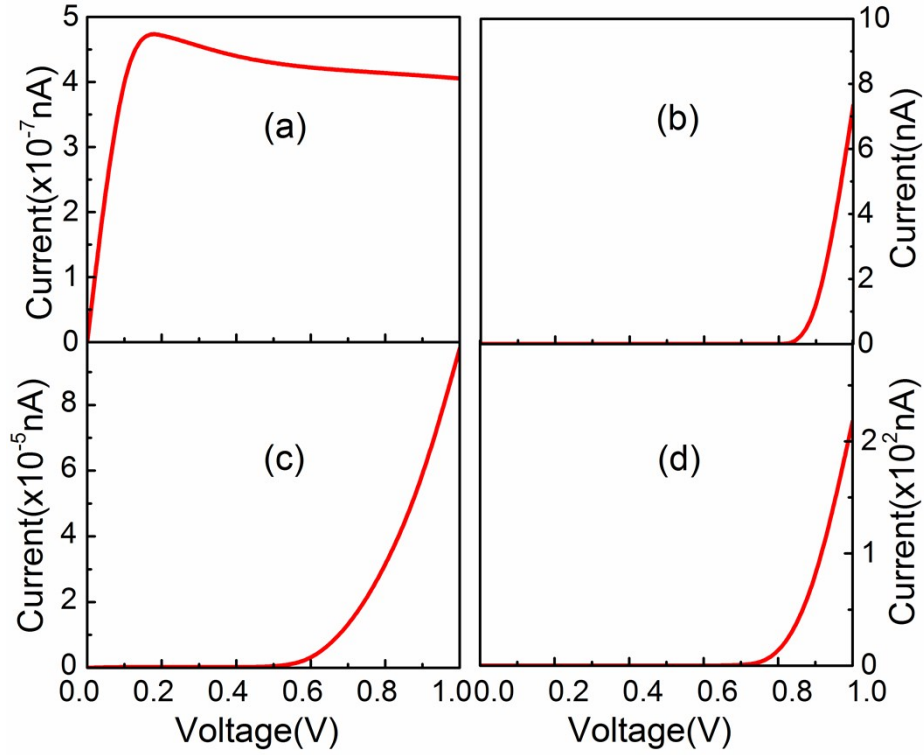


Fig. S1 The *I-V* curves of (a) GeS, (b) GeSe, (c) SnS, and (d) SnSe monolayers.

The 2D monolayers could present completely different electronic and transport properties from their 1D nanoribbons. Concretely, the conductance of GeSe/SnSe monolayer is larger than that of GeS/SnS, and the conductance of SnS/SnSe is larger than that of GeS/GeSe monolayer.